

EAST - [10600800.wsp.1]

File View Edit Tools Window Help

Drafts
 Pending
 Active
 L1: (2) ("5780341").PN.
 L2: (2) ("4957877").PN.
 L3: (2) ("5146426").PN.
 L4: (2) ("5432739").PN.
 L5: (2) ("5115289").PN.
 L6: (2) ("6479863").PN.
 L7: (2) ("6372617").PN.
 L8: (60726) "EPROM" or "EEPROM"
 L9: (2) "ent DIBL"
 Failed
 (0) 2 and ((folded near floating-gate) (folded near (floating adj gate)))
 (0) "EP"
 Saved
 (58084) (nonvolatile or non-volatile or non adj volatile) near memory
 (7902) ((nonvolatile or non-volatile or non adj volatile) near memory) and (floating-gate float
 (8) (((nonvolatile or non-volatile or non adj volatile) near memory) and (floating-gate floating
 (10) folded adj floating adj gate
 (60726) "EPROM" or "EEPROM"
 (10779) ("EPROM" or "EEPROM") and floating adj gate\$1
 (8) ("EPROM" or "EEPROM") and folded adj floating adj gate\$1
 (8) ("EPROM" or "EEPROM") and folded adj floating adj gate\$1
 Favorites
 Tagged (0)
 UDC
 Queue
 Trash

Queue
 US ☐ Plurals
 Default operator ☒ Highlight all hit terms initially
 8 and "DIBL"

BPS 164 3m Text HTML

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	<input type="checkbox"/>	US 6630724 B1	20031007	48	Gate dielectric antifuse circuits and methods for operating same	257/530	365/189.05; 365/189.09;
2	<input type="checkbox"/>	<input type="checkbox"/>	US 6510085 B1	20030121	11	Method of channel hot electron programming for short channel NOR flash	365/185.28	365/185.26; 365/185.33
3	<input type="checkbox"/>	<input type="checkbox"/>	US 6469939 B1	20021022	25	Flash memory device with increase of efficiency during an APDE (automatic	365/185.28	365/185.33
4	<input type="checkbox"/>	<input type="checkbox"/>	US 6466489 B1	20021015	20	Use of source/drain asymmetry MOSFET devices in dynamic and analog circuits	365/189.09	257/404
5	<input type="checkbox"/>	<input type="checkbox"/>	US 6440801 B1	20020827	73	Structure for folded architecture pillar memory cell	438/272	257/302; 257/330;
6	<input type="checkbox"/>	<input type="checkbox"/>	US 6420234 B1	20020716	14	Short channel length transistor and method of fabricating the same	438/259	257/E21.205; 257/E21.206;
7	<input type="checkbox"/>	<input type="checkbox"/>	US 6317357 B1	20011113	17	Vertical bipolar read access for low voltage memory cell	365/149	257/302; 365/177
8	<input type="checkbox"/>	<input type="checkbox"/>	US 6236595 B1	20010522	19	Programming method for a memory cell	365/185.18	
9	<input type="checkbox"/>	<input type="checkbox"/>	US 6188101 B1	20010213	5	Flash EPROM cell with reduced short channel effect and method for providing	257/314	257/315; 257/404;
10	<input type="checkbox"/>	<input type="checkbox"/>	US 6114725 A	20000905	74	Structure for folded architecture pillar memory cell	257/330	257/296; 257/301;
11	<input type="checkbox"/>	<input type="checkbox"/>	US 6087892 A	20000711	11	Target Ion/Ioff threshold tuning circuit and method	327/534	327/535; 327/540